## NXPS20H100C



# Dual power Schottky diode Rev. 2 — 8 June 2012

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a SOT78 (TO-220AB) plastic package.

#### 1.2 Features and benefits

- High junction temperature capability
- Low leakage current

- Negligible switching losses
- Optimised design to give low V<sub>F</sub> and high T<sub>j(max)</sub>

#### 1.3 Applications

- DC to DC converters
- Freewheeling diode

- OR-ing diode
- Switched mode power supply rectifier

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	100	V
I <sub>F(AV)</sub>	average forward current	square-wave pulse; $\bar{\delta} = 0.5$ ; $T_{mb} \le 163$ °C; per diode; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	10	Α
I <sub>O(AV)</sub>	average output current	square-wave pulse; $\delta = 0.5$ ; $T_{mb} \le 161$ °C; both diodes conducting	-	-	20	Α
Tj	junction temperature		-	-	175	°C
Static characte	eristics					
V <sub>F</sub>	forward voltage	$I_F = 10 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 6	-	-	0.77	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; see <u>Figure 6</u>	-	0.59	0.64	V
I <sub>R</sub>	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	2	4.5	μΑ
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 125 °C; see <u>Figure 7</u>	-	1	6	mA



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode	mb	A1
3	A2	anode 2		<u> </u>
mb	К	mounting base; cathode	1 2 3	sym125
			SOT78 (TO-220AB)	

## 3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
NXPS20H100C	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78	

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	100	V
I <sub>F(AV)</sub>	average forward current	square-wave pulse; $\delta = 0.5$ ; $T_{mb} \le 163$ °C; per diode; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	10	Α
I <sub>O(AV)</sub>	average output current	square-wave pulse; $\delta = 0.5$ ; $T_{mb} \le 161$ °C; both diodes conducting	-	20	Α
I <sub>FSM</sub>	non-repetitive peak forward current	sine-wave pulse; $t_p = 10 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$ ; see Figure 4	-	250	Α
T <sub>stg</sub>	storage temperature		-65	175	°C
T <sub>j</sub>	junction temperature		-	175	°C

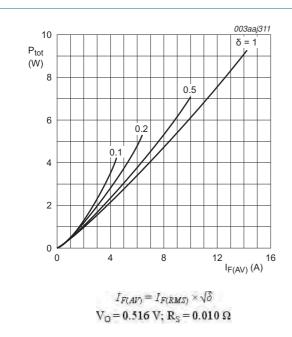


Fig 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

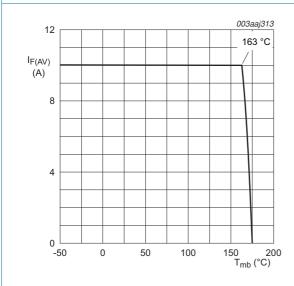


Fig 3. Average forward current as a function of mounting base temperature; per diode; maximum values

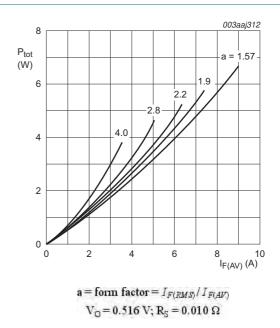


Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

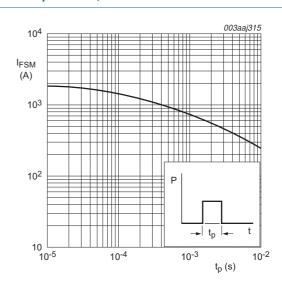


Fig 4. Non-repetitive peak forward current as a function of pulse width; square waveform; per diode; maximum values

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub> thermal resistance from junction to mounting base		with heatsink compound; per diode; see Figure 5	-	-	1.6	K/W
		with heatsink compound; both diodes conducting	-	-	0.9	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

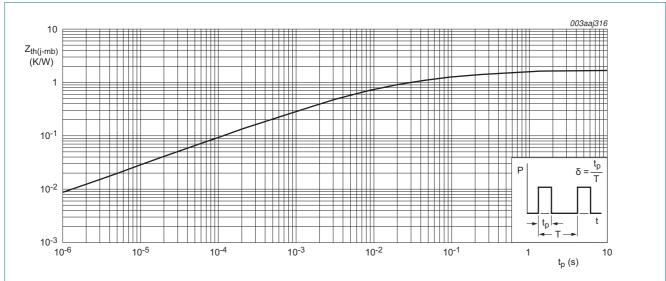
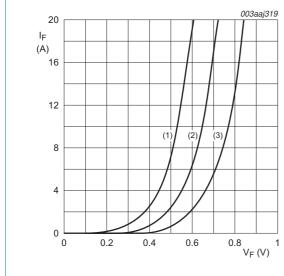


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse width; per diode

#### 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub> forward voltage	$I_F = 8 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 6	-	-	0.71	V	
		$I_F = 10 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 6	-	-	0.77	V
		$I_F = 16 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{\text{Minimum of 1}}$	-	-	0.81	V
		$I_F = 20 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{\text{Minimum of 1}}$	-	-	0.88	V
		$I_F = 8 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{\text{Minimum of 1}}$	-	0.56	0.58	V
	$I_F = 10 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{\text{ occ}}$	-	0.59	0.64	V	
		$I_F = 16 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{}$	-	0.65	0.68	V
		$I_F = 20 \text{ A}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{}$	-	0.67	0.73	V
I <sub>R</sub>	reverse current	$V_R = 100 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	2	4.5	μΑ
		$V_R = 100 \text{ V}; T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	-	1	6	mA
Dynamic ch	naracteristics					
C <sub>d</sub>	diode capacitance	$f = 1 \text{ MHz}$ ; $V_R = 10 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 8	-	250	-	рF



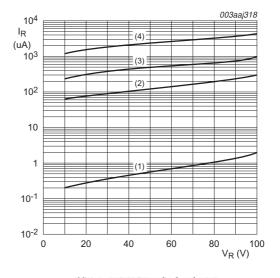
(1)  $T_j = 125$  °C; typical values;

(2) T<sub>i</sub> = 125 °C; maximum values;

(3)  $T_1 = 25$  °C; maximum values;

 $V_O = 0.516 \text{ V}; R_S = 0.010 \Omega$ 

Fig 6. Forward current as a function of forward voltage; per diode



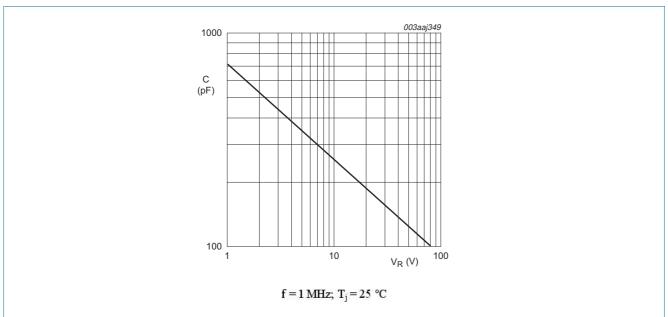
(1)  $T_j = 25$  °C; typical values;

(2) T<sub>i</sub> = 100 °C; typical values;

(3) T<sub>i</sub> = 125 °C; typical values;

(4)  $T_j = 150$  °C; typical values

Fig 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

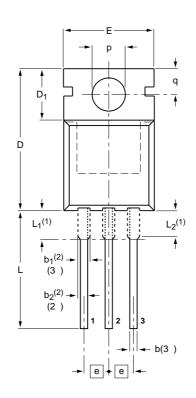


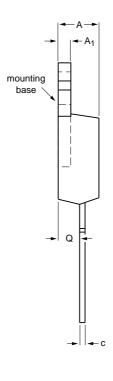
Junction capacitance as a function of applied reverse voltage; per diode; typical values

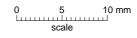
**SOT78** 

## 7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB







#### DIMENSIONS (mm are the original dimensions)

UNIT	A	<b>A</b> <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> (1)	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION		ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

Fig 9. Package outline SOT78 (TO-220AB)

NXPS20H100C

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## **Revision history**

#### Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
NXPS20H100C v.2	20120608	Product data sheet	-	NXPS20H100C v.1
Modifications:	<ul><li>Status change</li><li>Various change</li></ul>	d from preliminary to produces to content.	t.	
NXPS20H100C v.1	20120420	Preliminary data shee	t -	-

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Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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#### **Dual power Schottky diode**

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